

Form PTO 1449

(Modified)

U.S. DEPARTMENT OF  
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DOCKET NO.

2343-137-27

APPLICANT

Jeffrey B. CASADY, et al.

SERIAL NO.

10/033,785

LIST OF REFERENCES CITED BY APPLICANT  
(Use Several Sheets if Necessary)

FILING DATE

January 3, 2002

GROUP ART UNIT

2811

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
Jmz	AA	6,410,396B1	6/25/02	Casady, et al.			
	AB						
	AC						
	AD						
	AE						

## FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO
	AF				
	AG				

## OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)

Jmz	AH	Trivedi, M., et al., "Comparison of RF Performance of Vertical and Lateral DMOSFET", IEEE Int'l Symposium on Power Semiconductor Devices and ICs, p. 245-248, May 1999.
	AI	Mazzola, M.S., et al., "Close Compensation of 6H and 4H Silicon Carbide By Silicon-to-Carbon Ratio Control", Materials Science and Engineering, pp. 155-157, 1999.
	AJ	Mazzola, M.S., et al., "Boron Compensation of 6H Silicon Carbide", Materials Science Forum, Vols. 264-268, pp.119-122, 1998.
	AK	Hiraoka, Y., et al., "Comparison of High-Frequency Performance of Quasi-SOI and Conventional SOI Power MOSFETs", 2000 International Symposium on Power Semiconductor Devices and IC's, p. 161-164, May 22-25 2000.
	AL	Ludikhuizen, A.W., "A Review of RESURF Technology", 2000 International Symposium on Power Semiconductor Devices and IC's, p. 11-18, May 22-25, 2000.
	AM	Tan, Y., et al., "A SOI LDMOS/CMOS/BJT Technology for Fully-Integrated RF Power Amplifiers", 2000 International Symposium on Power Semiconductor Devices and IC's, p. 137-140, May 22-25 2000.
✓	AN	Spitz, J., et al., "High-Voltage (2.6 kV) Lateral DMOSFETs in 4H-SiC", Materials Science Forum, Vols. 264-268, pp. 1005-1008, 1998.
	AO	

EXAMINER

DATE CONSIDERED Dec 8, 2002

\*EXAMINER: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.